

Fast Thyristor/Diode and Thyristor/Thyristor (MAGN-A-PAK™ Power Modules), 200 A



MAGN-A-PAK™

FEATURES

- Fast turn-off thyristor
- Fast recovery diode
- High surge capability
- Electrically isolated baseplate
- 3500 V_{RMS} isolating voltage
- Industrial standard package
- Lead (Pb)-free
- Designed and qualified for industrial level


RoHS
COMPLIANT

PRODUCT SUMMARY

$I_{T(AV)}$	200 A
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DESCRIPTION

This series of MAGN-A-PAK™ modules are intended for applications such as self-commutated inverters, DC choppers, electronic welders, induction heating and others where fast switching characteristics are required.

MAJOR RATINGS AND CHARACTERISTICS

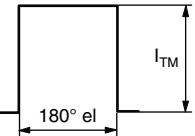
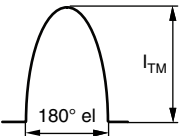
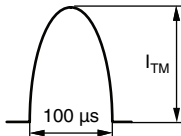
SYMBOL	CHARACTERISTICS	VALUES	UNITS
$I_{T(AV)}$		200	A
	T_C	85	°C
$I_{T(RMS)}$		444	A
I_{TSM}	50 Hz	7600	
	60 Hz	8000	
I^2t	50 Hz	290	kA ² s
	60 Hz	265	
$I^2\sqrt{t}$		2900	kA ² √s
t_q		20/25	μs
t_{rr}		2	
V_{DRM}/V_{RRM}		up to 1200	V
T_J	Range	- 40 to 125	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS

TYPE NUMBER	VOLTAGE CODE	V_{RRM}/V_{DRM} , MAXIMUM REPETITIVE PEAK REVERSE AND OFF-STATE BLOCKING VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I_{RRM}/I_{DRM} AT $T_J = 125^\circ\text{C}$ mA
VSK.F200-	08	800	800	50
	12	1200	1200	

CURRENT CARRYING CAPABILITY

FREQUENCY							UNITS
50 Hz	380	560	630	850	2460	3180	A
400 Hz	460	690	710	1060	1570	2080	
2500 Hz	310	450	530	760	630	860	
5000 Hz	250	360	410	560	410	560	
10 000 Hz	180	280	300	410	-	-	
Recovery voltage V_r	50	50	50	50	50	50	V
Voltage before turn-on V_d	80 % V_{DRM}		80 % V_{DRM}		80 % V_{DRM}		
Rise of on-state current di/dt	50	50	-	-	-	-	A/μs
Case temperature	85	60	85	60	85	60	°C
Equivalent values for RC circuit	10/0.47		10/0.47		10/0.47		Ω/μF

ON-STATE CONDUCTION

PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS	
Maximum average on-state current at case temperature	I _{T(AV)}	180° conduction, half sine wave			200	A	
					85	°C	
Maximum RMS on-state current	I _{T(RMS)}	As AC switch			444	A	
Maximum peak, one-cycle non-repetitive on-state, surge current	I _{TSM}	t = 10 ms	No voltage reapplied	Sinusoidal half wave, initial T _J = 125 °C	7600		
		t = 8.3 ms			8000		
		t = 10 ms	100 % V _{RRM} reapplied		6400		
		t = 8.3 ms			6700		
Maximum I ² t for fusing	I ² t	t = 10 ms	No voltage reapplied		290	kA ² s	
		t = 8.3 ms			265		
		t = 10 ms	100 % V _{RRM} reapplied		205		
		t = 8.3 ms			187		
Maximum I ² √t for fusing	I ² √t	t = 0.1 to 10 ms, no voltage reapplied			2900	kA ² √s	
Low level value or threshold voltage	V _{T(TO)1}	(16.7 % × π × I _{T(AV)} < I < π × I _{T(AV)}), T _J = T _J maximum			1.18	V	
High level value of threshold voltage	V _{T(TO)2}	(I > π × I _{T(AV)} < I < π × I _{T(AV)}), T _J = T _J maximum			1.25		
Low level value on-state slope resistance	r _{t1}	(16.7 % × π × I _{T(AV)} < I < π × I _{T(AV)}), T _J = T _J maximum			0.74	mΩ	
High level value on-state slope resistance	r _{t2}	(I > π × I _{T(AV)} < I < π × I _{T(AV)}), T _J = T _J maximum			0.70		
Maximum on-state voltage drop	V _{TM}	I _{pk} = 600 A, T _J = T _J maximum, t _p = 10 ms sine pulse			1.73	V	
Maximum holding current	I _H	T _J = 25 °C, I _T > 30 A			6000	mA	
Maximum latching current	I _L	T _J = 25 °C, V _A = 12 V, R _a = 6 Ω, I _g = 1A			1000		

**SWITCHING**

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES		UNITS
			K	J	
Maximum non-repetitive rate of rise	di/dt	Gate drive 20 V, 20 Ω , $t_r \leq 1$ ms, $V_D = 80\% V_{DRM}$, $T_J = 25^\circ\text{C}$	800		A/ μs
Maximum recovery time	t_{rr}	$I_{TM} = 350$ A, $di/dt = -25$ A/ μs , $V_R = 50$ V, $T_J = 25^\circ\text{C}$	2		μs
Maximum turn-off time	t_q	$I_{TM} = 750$ A; $T_J = T_J$ maximum; $di/dt = -25$ A/ μs ; $V_R = 50$ V; $dV/dt = 400$ V/ μs linear to $80\% V_{DRM}$	20	25	

BLOCKING

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = 125^\circ\text{C}$, exponential to $67\% V_{DRM}$	1000	V/ μs
RMS insulation voltage	V_{INS}	50 Hz, circuit to base, $T_J = 25^\circ\text{C}$, $t = 1$ s	3000	V
Maximum peak reverse and off-state leakage current	I_{RRM} , I_{DRM}	$T_J = 125^\circ\text{C}$, rated V_{DRM}/V_{RRM} applied	50	mA

TRIGGERING

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P_{GM}	$f = 50$ Hz, $d\% = 50$	60	W
Maximum peak average gate power	$P_{G(AV)}$	$T_J = 125^\circ\text{C}$, $f = 50$ Hz, $d\% = 50$	10	
Maximum peak positive gate current	I_{GM}	$T_J = 125^\circ\text{C}$, $t_p \leq 5$ ms	10	A
Maximum peak negative gate voltage	$-V_{GT}$		5	V
Maximum DC gate current required to trigger	I_{GT}	$T_J = 25^\circ\text{C}$, $V_{ak} 12$ V, $R_a = 6$	200	mA
DC gate voltage required to trigger	V_{GT}		3	V
DC gate current not to trigger	I_{GD}	$T_J = 125^\circ\text{C}$, rated V_{DRM} applied	20	mA
DC gate voltage not to trigger	V_{GD}		0.25	V

THERMAL AND MECHANICAL SPECIFICATIONS

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction operating temperature range	T _J		- 40 to 125	°C
Storage temperature range	T _{Stg}		- 40 to 150	
Maximum thermal resistance, junction to case per junction	R _{thJC}	DC operation	0.125	K/W
Maximum thermal resistance, case to heatsink per module	R _{thC-hs}	Mounting surface flat, smooth and greased	0.025	
Mounting torque ± 10 % MAP to heatsink busbar to MAP		A mounting compound is recommended. The torque should be rechecked after a period of 3 hours to allow for the spread of the compound. Use of cable lugs is not recommended, busbar should be used and restrained during tightening. Threads must be lubricated with a compound.	4 to 6 (35 to 53)	N · m (lbf · in)
Approximate weight			500	g
			17.8	oz.

ΔR_{thJC} CONDUCTION			
CONDUCTIONS ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	UNITS
180°	0.009	0.006	K/W
120°	0.10	0.011	
90°	0.014	0.015	
60°	0.020	0.020	
30°	0.32	0.033	

Note

- Table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

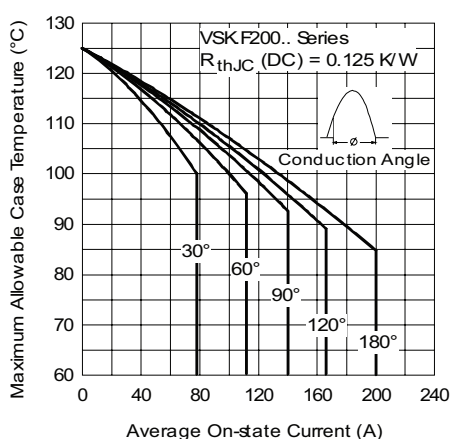


Fig. 1 - Current Ratings Characteristics

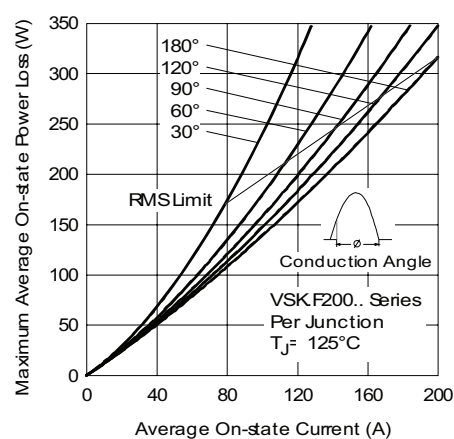


Fig. 3 - On-State Power Loss Characteristics

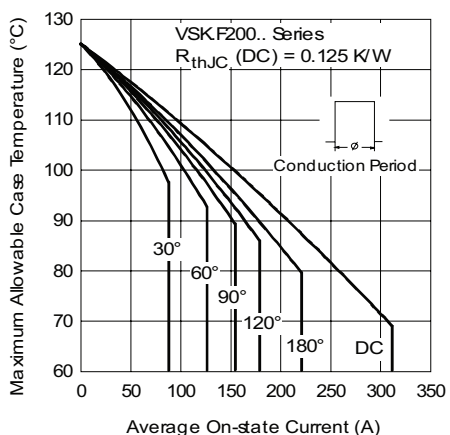


Fig. 2 - Current Ratings Characteristics

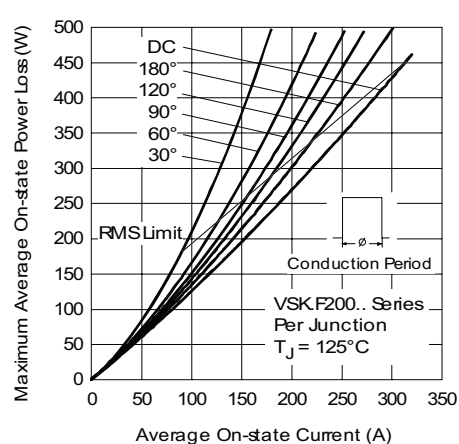


Fig. 4 - On-State Power Loss Characteristics

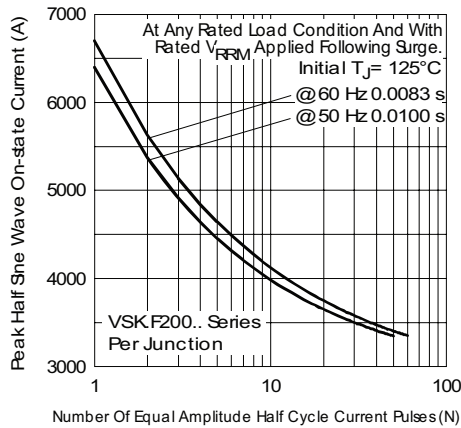


Fig. 5 - Maximum Non-Repetitive Surge Current

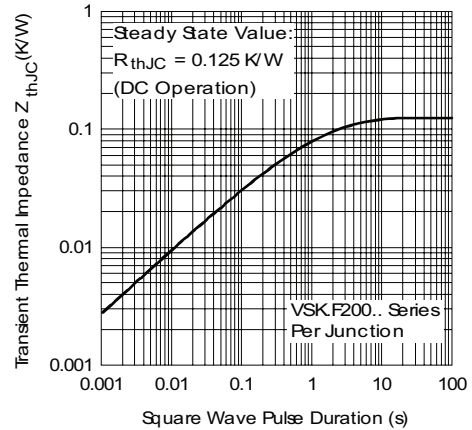


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

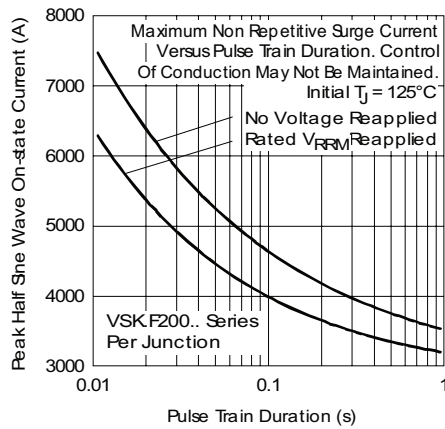


Fig. 6 - Maximum Non-Repetitive Surge Current

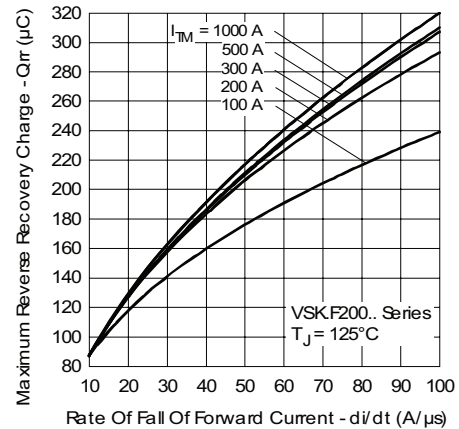


Fig. 9 - Reverse Recovery Charge Characteristics

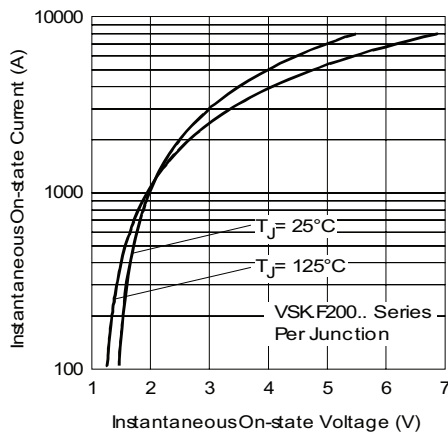


Fig. 7 - On-State Voltage Drop Characteristics

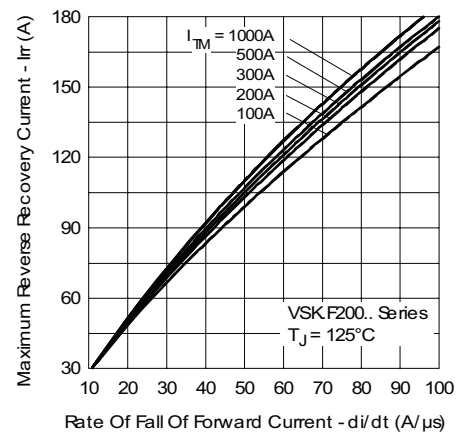


Fig. 10 - Reverse Recovery Current Characteristics

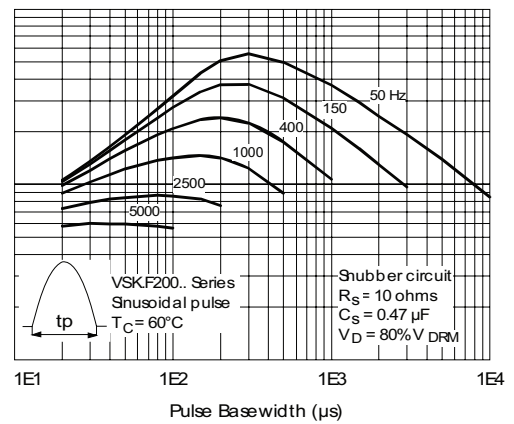
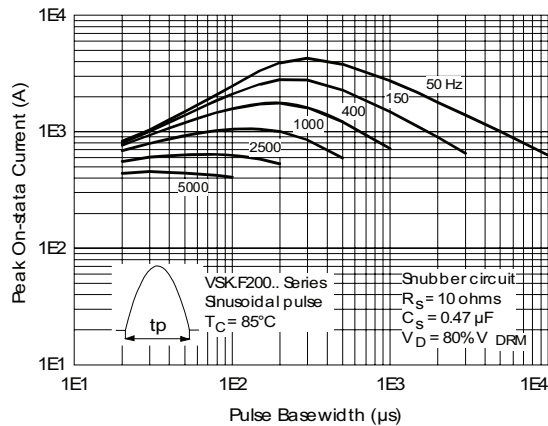


Fig. 11 - Frequency Characteristics

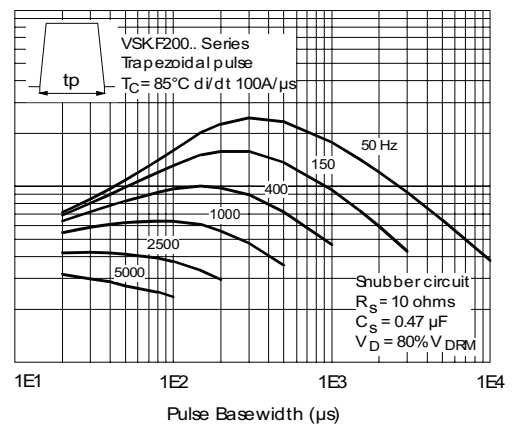
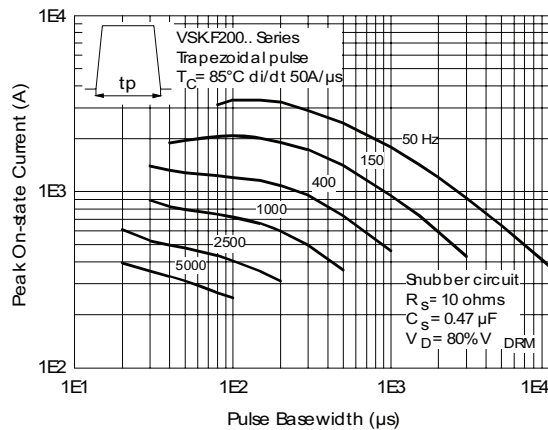


Fig. 12 - Frequency Characteristics

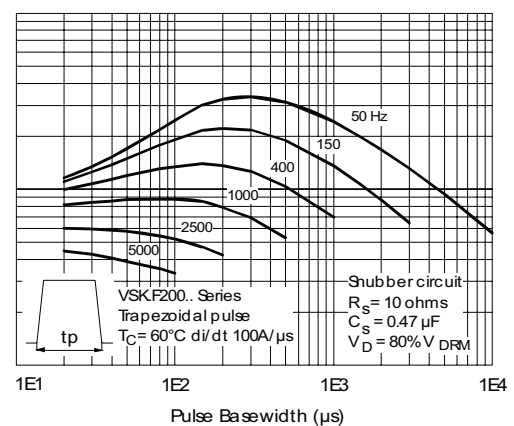
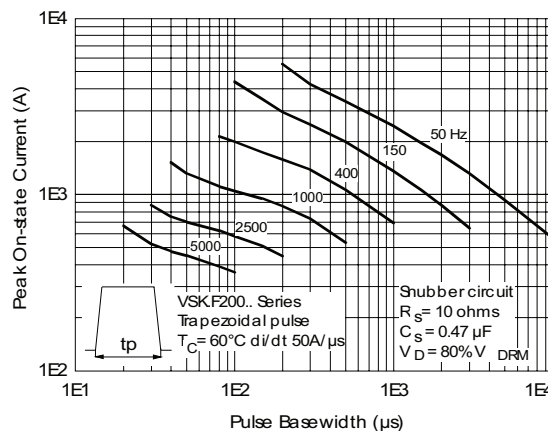


Fig. 13 - Frequency Characteristics

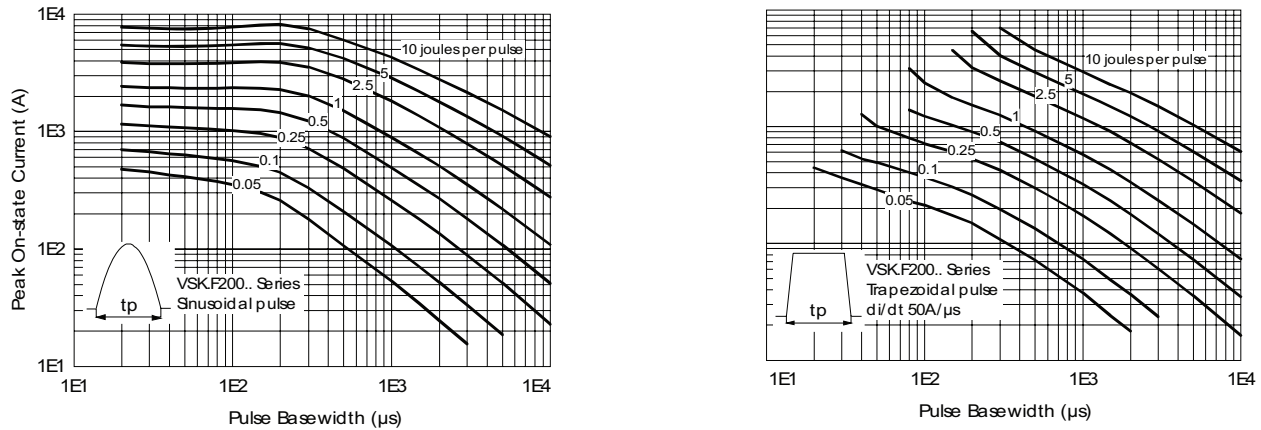


Fig. 14 - Maximum On-State Energy Power Loss Characteristics

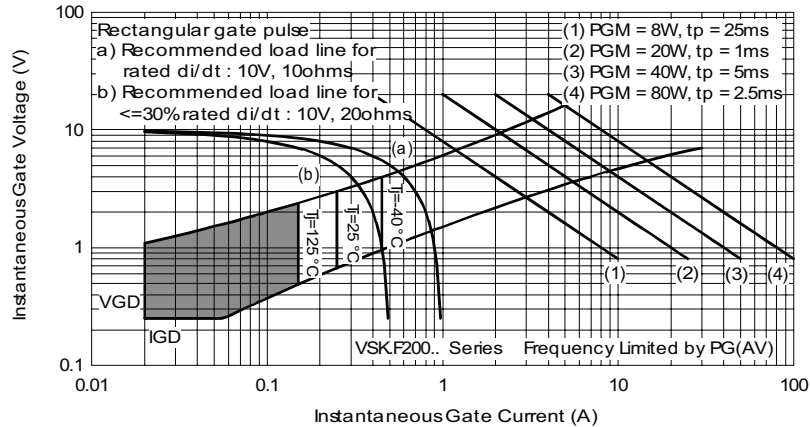


Fig. 15 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	VSK	T	F	200	-	12	H	K	P
	1	2	3	4		5	6	7	8
1	Module type								
2	Circuit configuration								
3	Fast SCR								
4	Current rating: $I_{T(AV)} \times 10$ rounded								
5	Voltage code $\times 100 = V_{RRM}$ (see Voltage Ratings table)								
6	dV/dt code: $H \leq 400 \text{ V}/\mu\text{s}$								
7	t_q code: $K \leq 20 \mu\text{s}$ $J \leq 25 \mu\text{s}$								
8	Lead (Pb)-free								

Note

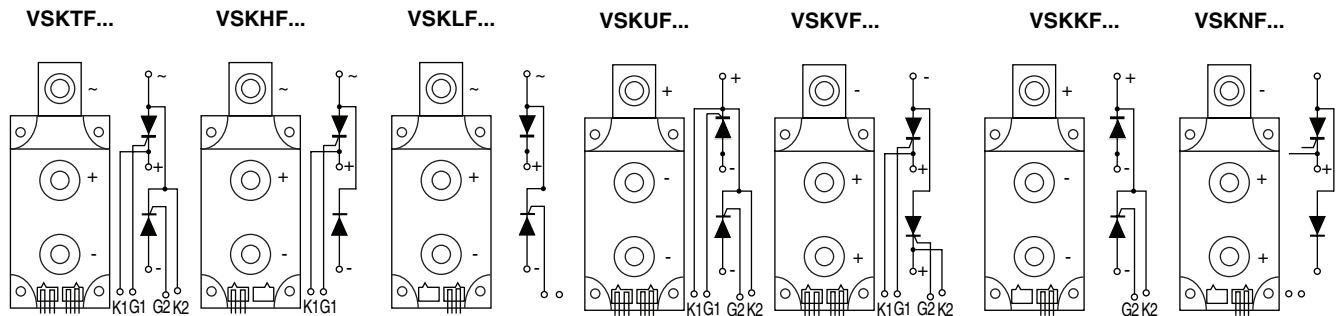
- To order the optional hardware go to www.vishay.com/doc?95172

VSK.F200..P Series



Vishay High Power Products Fast Thyristor/Diode and Thyristor/Thyristor
(MAGN-A-PAK™ Power Modules), 200 A

CIRCUIT CONFIGURATION



LINKS TO RELATED DOCUMENTS

Dimensions	http://www.vishay.com/doc?95086
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